TOSHIBA CMOS Digital Integrated Circuit Silicon Monolithic

# TC7SH34FE

#### **NON-INVERT BUFFER**

#### **Features**

• Super high speed operation :tpD = 3.8 ns (typ.)

 $@V_{CC} = 5 V$ 

• Low power dissipation :  $I_{CC} = 2 \mu A$  (Max.)

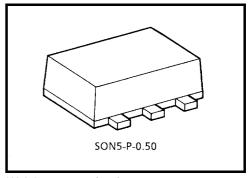
@ Ta = 25°C

• High noise immunity :  $V_{NIH} = V_{NIH}$ 

= 28% V<sub>CC</sub> (Min.)

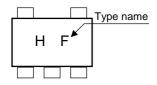
• 5.5V tolerant input.

• Wide operation voltage range : VCC (opr) = 2~5.5 V

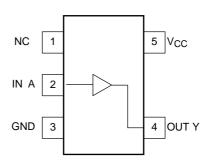


Weight: 0.003 g (typ.)

#### Marking



### Pin Assignment (top view)

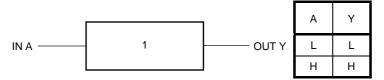


#### **Maximum Ratings (Ta = 25°C)**

Characteristics	Symbol	Rating	Unit
Supply voltage range	V <sub>CC</sub>	-0.5~7	V
DC input voltage	V <sub>IN</sub>	-0.5~7	V
DC output voltage	Vout	-0.5~V <sub>CC</sub> + 0.5	V
Input diode current	lικ	-20	mA
Output diode current	lok	±20	mA
DC output current	lout	±25	mA
DC V <sub>CC</sub> /ground current	Icc	±50	mA
Power dissipation	P <sub>D</sub>	150	mW
Storage temperature	T <sub>stg</sub>	-65~150	°C

# **Logic Diagram**

#### **Truth Table**



# **Recommended Operating Conditions**

Characteristics	Symbol	Rating	Unit
Supply voltage	V <sub>CC</sub>	2~5.5	V
Input voltage	V <sub>IN</sub>	0~5.5	V
Output voltage	V <sub>OUT</sub>	0~ V <sub>CC</sub>	V
Operating temperature	T <sub>opr</sub>	-40~85	°C
Input rise and fall time	dt/dv	0~100 ( $V_{CC}$ = 3.3 V $\pm$ 0.3 V )	ns/V
input rise and rail time	avav	0~20 ( $V_{CC}$ = 5 $V$ ± 0.5 $V$ )	113/ V

# **Electrical Characteristics**

# **DC Characteristics**

Characteristics Symbol Test Circuit		Test	Test Condition			Ta = 25°C			Ta = -40~85°C		Unit
		rest Condition		V <sub>CC</sub> (V)	Min	Тур.	Max	Min	Max	Onit	
High-level input voltage VIH —					2.0	1.5	_	_	1.5	_	
		_		3.0~5.5	V <sub>CC</sub> × 0.7			V <sub>CC</sub> × 0.7	ı	V	
Low-level input				2.0	_	_	0.5	_	0.5		
voltage	V <sub>IL</sub>	_	_		3.0~5.5	_	_	V <sub>CC</sub> × 0.3	_	V <sub>CC</sub> × 0.3	V
High-level output voltage VOH				2.0	1.9	2.0		1.9			
			V <sub>IN</sub> = V <sub>IH</sub>	I <sub>OH</sub> = -50 μA	3.0	2.9	3.0		2.9		V
	V <sub>OH</sub>	_			4.5	4.4	4.5		4.4		
				$I_{OH} = -4 \text{ mA}$	3.0	2.58	_		2.48		
				$I_{OH} = -8 \text{ mA}$	4.5	3.94	_	_	3.80	_	
Low-level output voltage		$V_{IN} = V_{IL}$	I <sub>OL</sub> = 50 μA	2.0	—	0	0.1		0.1	V	
				3.0	—	0	0.1		0.1		
	_			4.5	—	0	0.1		0.1		
			I <sub>OL</sub> = 4 mA	3.0	_	_	0.36	_	0.44		
			$I_{OL} = 8 \text{ mA}$	4.5	_	_	0.36	_	0.44		
Input leakage current	I <sub>IN</sub>	_	V <sub>IN</sub> = 5.5 V	or GND	0~5.5	_	_	±0.1	_	±1.0	μА
Quiescent supply current	Icc	_	V <sub>IN</sub> = V <sub>CC</sub> o	or GND	5.5	_	_	2.0	_	20.0	μА

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# AC Characteristics (input: $t_r = t_f = 3 \text{ ns}$ )

Characteristics	Symbol	Test Condition			Ta = 25°C			Ta = -40~85°C		- Unit
			V <sub>CC</sub> (V)	C <sub>L (</sub> pF)	Min	Тур.	Max	Min	Max	Unit
Propagation delay time	<sup>t</sup> PLH t <sub>PHL</sub>	3.3 ± 0.3	15	_	5.0	7.1	1.0	8.5		
			3.3 ± 0.3	50	_	7.5	10.6	1.0	12.0	- ns
			5.0 ± 0.5	15	_	3.8	5.5	1.0	6.5	
		5.0 ± 0.5	50	_	5.3	7.5	1.0	8.5		
Input capacitance	C <sub>IN</sub>					4	10	_	10	pF
Power dissipation capacitance	C <sub>PD</sub>		(Note)		_	13	_	_	_	pF

Note: C<sub>PD</sub> is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation.

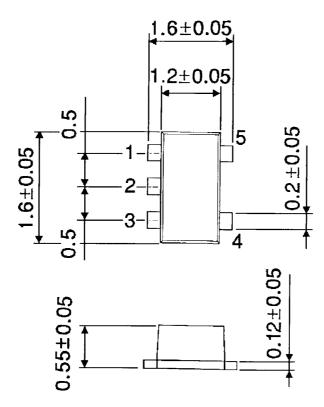
$$I_{CC (opr)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}$$

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# **Package Dimensions**

SON5-P-0.50 Unit: mm



Weight: 0.003 g (typ.)

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Handbook" etc..

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